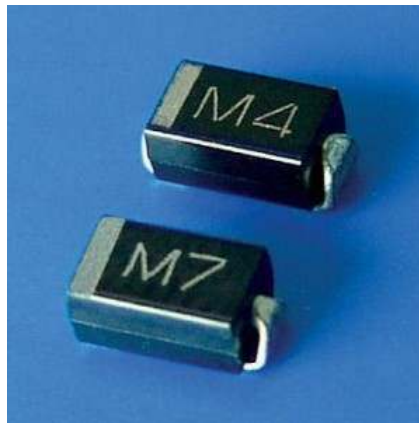




### SMD Silicon Rectifiers Diodes M1 M2 M3 M4 M5 M6 M7



#### Specifications

1A SMD Silicon Rectifiers Diodes M1 M2 M3 M4 M5 M6 M7 DO-214AC(SMA)

SMD Diode M1 M2 M3 M4 M5 M6 M7

Pb-free, Halogen-free

#### Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	M1	M2	M3	M4	M5	M6	M7	Units
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @ $T_L = 110\text{ }^\circ\text{C}$	$I_{(AV)}$	1.0							A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	$I_{FSM}$	40						30	A
Maximum Instantaneous Forward Voltage @ 1.0A	$V_F$	1.1							V
Maximum DC Reverse Current @ $T_A = 25\text{ }^\circ\text{C}$ at Rated DC Blocking Voltage @ $T_A = 125\text{ }^\circ\text{C}$	$I_R$	5.0							uA
Typical Reverse Recovery Time (Note 1)	$T_{rr}$	1.5							uS
Typical Junction Capacitance ( Note 2 )	$C_j$	12							pF
Non-Repetitive Peak Reverse Avalanche Energy at 25°C, $I_{AS}=1\text{A}$ , $L=10\text{mH}$	$E_{AS}$	5							mJ
Typical Thermal Resistance (Note 3)	$R_{\theta JL}$ $R_{\theta JA}$	27 75					30 85		$^\circ\text{C/W}$
Operating Temperature Range	$T_J$	-55 to +150							$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 to +150							$^\circ\text{C}$

- Notes:
- Reverse Recovery Test Conditions:  $I_r=0.5\text{A}$ ,  $I_s=1.0\text{A}$ ,  $I_{rr}=0.25\text{A}$
  - Measured at 1 MHz and Applied  $V_A=4.0\text{ Volts}$
  - Measured on P.C. Board with 0.2" x 0.2" (5.0mm x 5.0mm) Copper Pad Areas.